

MOS FIELD EFFECT TRANSISTOR 2SK2857

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR HIGH SPEED SWITCHING

DESCRIPTION

The 2SK2857 is a switching device which can be driven directly by a 5V power source.

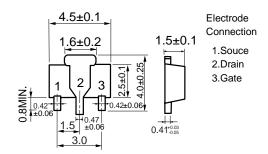
The 2SK2857 features a low on-state resistance and excellent Switching Characteristics, and is suitable for applications such as actuator driver.

FEATURES

- Can be driven by a 5V power source.
- Low On-state resistance :

 $R_{DS(on)1} = 220 \text{ m}\Omega \text{ MAX. (VGs} = 4 \text{ V, ID} = 1.5 \text{ A)}$ $R_{DS(on)2} = 150 \text{ m}\Omega \text{ MAX. (VGs} = 10 \text{ V, ID} = 2.5 \text{ A)}$

PACKAGE DRAWING (Unit: mm)



Marking: NX

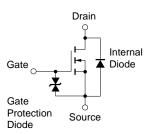
ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

Drain to Source Voltage	VDSS	60	V
Gate to Source Voltage	Vgss	±20	V
Drain Current (DC)	I _{D(DC)}	±4	Α
Drain Current (pulse) Note1	D(pulse)	±16	Α
Total Power Dissipation Note2	Pτ	2	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Notes1. PW \leq 10 μ s, Duty Cycle \leq 1 %

2. Mounted on ceramic board of 16 cm² \times 0.7 mm

EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device is actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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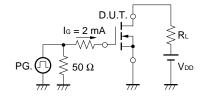
ELECTRICAL CHARACTERISTICS (TA = 25 °C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	V _{DS} = 60 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	Vgs = ±20 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	VGS(off)	VDS = 10 V, ID = 1 mA	1.0	1.4	2.0	V
Forward Transfer Admittance	y fs	V _{DS} = 10 V, I _D = 2 A	1			S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 4 V, ID = 1.5 A		150	220	mΩ
	RDS(on)2	V _G S = 10 V, I _D = 2.5 A		110	150	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		265		pF
Output Capacitance	Coss	V _G s = 0 V		125		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		56		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 25 V, I _D = 1 A		8		ns
Rise Time	tr	$V_{GS(on)} = 10 \text{ V}, \text{ Rg} = 10 \Omega$		11		ns
Turn-off Delay Time	td(off)	RL = 25 Ω		52		ns
Fall Time	tr			22		ns
Total Gate Charge	Q _G	V _{DS} = 48 V		10.6		nC
Gate to Source Charge	Qgs	Vgs = 10 V		0.7		nC
Gate to Drain Charge	Q _{GD}	ID = 4 A		3.5		nC
Diode Forward Voltage	V _{F(S-D)}	IF = 4 A, VGS = 0 V		0.86		٧
Reverse Recovery Time	trr	IF = 4 A, VGS = 0 V		49		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A /μs		26.6		nC

TEST CIRCUIT 1 SWITCHING TIME

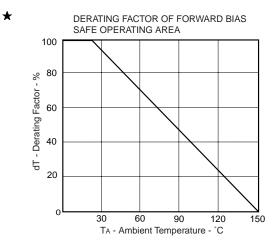
PG. \bigcap RG RG = 10 Ω \bigcap VDD \bigcap VGS \bigcap VG

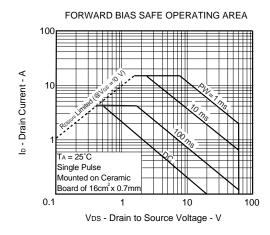
TEST CIRCUIT 2 GATE CHARGE

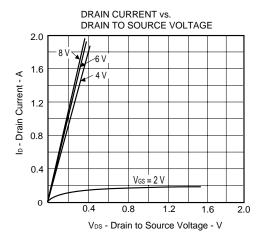


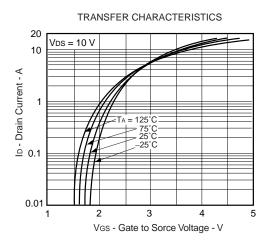


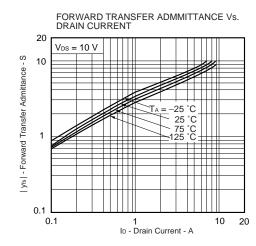
TYPICAL CHARACTERISTICS (TA = 25°C)

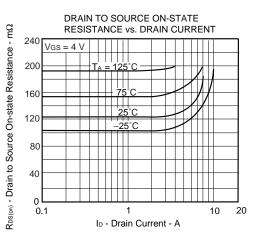




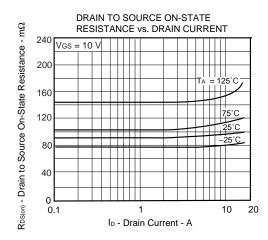


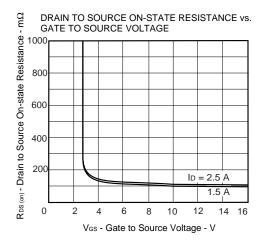


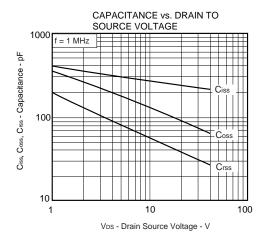


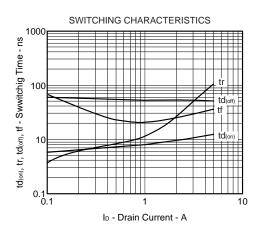


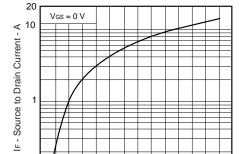
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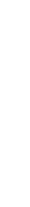






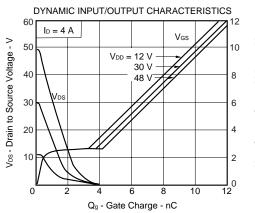


SOURCE TO DRAIN DIODE FORWARD VOLTAGE



1.8 2.0

1.6



Vos- Gate to Source Voltage - V

0.1 0.6

8.0

1.0

1.2 1.4

VF(S-D) - Source to Drain Voltage - V



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